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# N-Channel 60-V (D-S) MOSFET

PRODU	CT SUMMARY	
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)
60	0.072 at V <sub>GS</sub> = 10 V	5

#### **FEATURES**

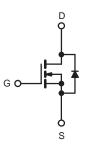
- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



RoHS COMPLIANT



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T <sub>A</sub> = 25 °C, unle	ss otherwise r	noted	
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	± 20	] v
Continuous Drain Current (T <sub>.I</sub> = 175 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	5	
Continuous Diam Current (1) = 175 C)	T <sub>A</sub> = 70 °C	טי	3.1	Α
Pulsed Drain Current		I <sub>DM</sub>	20	
Avalanche Current		I <sub>AS</sub>	4.8	
Single Pulse Avalanche Energy	E <sub>AS</sub>	8	mJ	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.3	W
Maximum Power Dissipation	T <sub>A</sub> = 70 °C	. п	2.3	• • • • • • • • • • • • • • • • • • • •
Operating Junction and Storage Temperature Range	ge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Mariana la Ambiant	t ≤ 10 s	R <sub>thJA</sub>	36	45			
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' thJA	75	90	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	17	20			

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.



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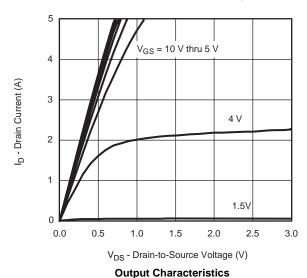
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•			
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	= 0 V, I <sub>D</sub> = 250 μA 60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zoro Coto Voltago Droin Current	I <sub>DSS</sub>	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$	= 0 V		1		
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			20	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
D : 0 0 0 1 D : 1 3	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$	0.072 0.089		0.089		
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = 10 \text{ V}, I_D = 2 \text{ A}, T_J = 125 ^{\circ}\text{C}$		0.090	0.120	Ω	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 3 \text{ A}$		7		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 3 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Dynamic <sup>b</sup>				•			
Total Gate Charge	$Q_g$			16	27		
Gate-Source Charge	Q <sub>gs</sub> Q <sub>gd</sub>	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 3 \text{ A}$		3.5		nC	
Gate-Drain Charge				5.1			
Gate Resistance	$R_g$	$V_{GS} = 0.1 \text{ V, f} = 5 \text{ MHz}$	0.5	1.4	2.4	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			12	20		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 30 $\Omega$		10	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 3 A$ , $V_{GEN} = 10 V$ , $R_g = 6 \Omega$		28	50	ns	
Fall Time	t <sub>f</sub>			12	24		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = 3 \text{ A}, dI/dt = 100 \text{ A/}\mu\text{s}$		55	80		

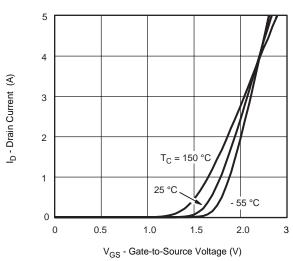
#### Notes:

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





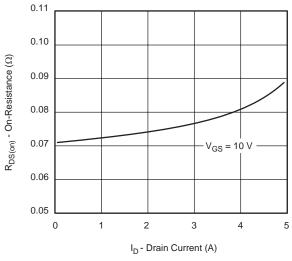
**Transfer Characteristics** 



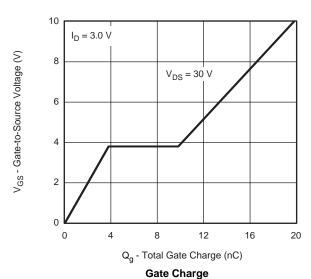
I<sub>S</sub> - Source Current (A)

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### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



T<sub>J</sub> = 175 °C  $T_{J} = 175$  °C  $T_{J} = 25$  °C

0.0

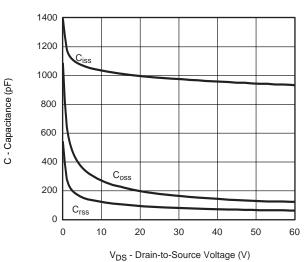
0.7

0.8

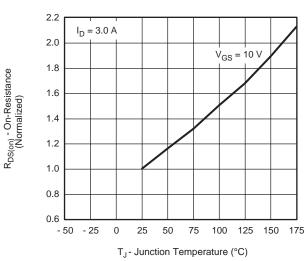
0.9

1.1  $V_{SD}$ - Source-to-Drain Voltage (V)

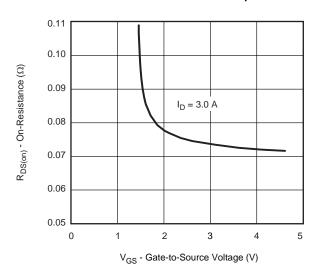
Source-Drain Diode Forward Voltage



Capacitance



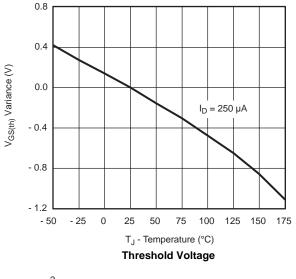
On-Resistance vs. Junction Temperature

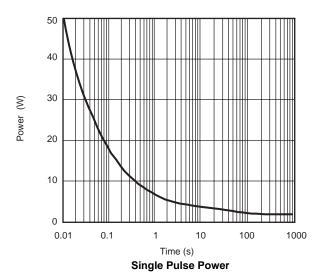


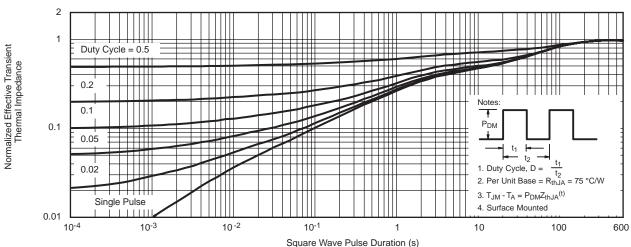
On-Resistance vs. Gate-to-Source Voltage

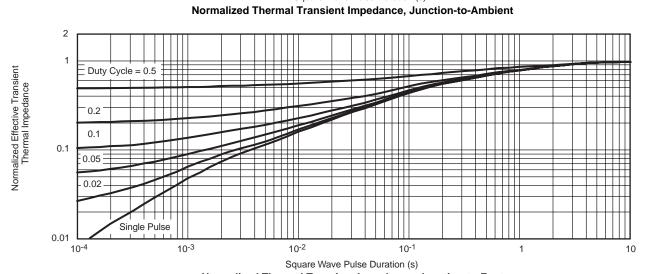


## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



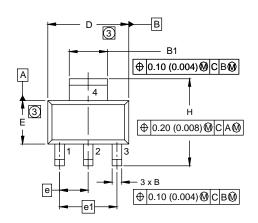


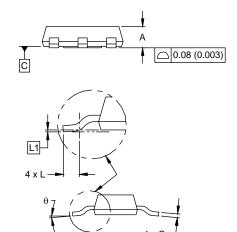






## **SOT-223 (HIGH VOLTAGE)**





DIM.	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
Α	1.55	1.80	0.061	0.071	
В	0.65	0.85	0.026	0.033	
B1	2.95	3.15	0.116	0.124	
С	0.25	0.35	0.010	0.014	
D	6.30	6.70	0.248	0.264	
E	3.30	3.70	0.130	0.146	
е	2.30 BSC		0.0905	BSC	
e1	4.60 BSC		0.181	BSC	
Н	6.71	7.29	0.264	0.287	
L	0.91	-	0.036	-	
L1	0.061 BSC		0.0024	1 BSC	
θ	-	10'	-	10'	

ECN: S-82109-Rev. A, 15-Sep-08

DWG: 5969

#### Notes

- 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
- 2. Dimensions are shown in millimeters (inches).
- 3. Dimension do not include mold flash.
- 4. Outline conforms to JEDEC outline TO-261AA.





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